VS-U5FH300FA60

Vishay Semiconductors



FRED Pt[®] Gen 5 Ultrafast Rectifier Diode, 600 V, 300 A

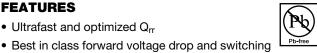


PRIMARY CHARACTERISTICS							
V _R	600 V						
V _F (typical) at 150 A, per diode	1.36 V						
t _{rr} (typical) at 150 A, per diode	76 ns						
$I_{F(DC)}$ per module at $T_C = 98 \ ^{\circ}C$	300 A						
Туре	Modules - diode, FRED Pt®						
Package	SOT-227						
Circuit configuration	Two separate diodes, parallel pin-out						

FEATURES

losses trade off

Ultrafast and optimized Q_{rr}



- RoHS COMPLIANT
- Optimized for high speed operation
- 175 °C maximum operating junction temperature
- · Electrically isolated base plate
- Large creepage distance between terminal
- · Simplified mechanical designs, rapid assembly
- Designed and gualified for industrial level
- UL approved file E78996
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

Featuring a unique combination of low conduction and switching losses, the VS-U5FH300FA60 is the right choice for high frequency converters, both soft switched / resonant. The semiconductor in the SOT-227 package is isolated from the copper base plate, allowing for common heatsinks and compact assemblies to be built.

These modules are specifically designed to improve efficiency of PFC and output rectification stages of EV / HEV battery charging stations, booster stage of solar inverters, and UPS applications, these devices are perfectly matched to operate with MOSFETs or high speed IGBTs.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Cathode to anode voltage	V _R		600	V			
Continuous forward current per diode	I _F	T _C = 98 °C	150	۸			
Single pulse forward current per diode	I _{FSM}	T _J = 25 °C	1080	A			
Maximum power dissipation per module	PD	T _C = 98 °C	440	W			
RMS isolation voltage	V _{ISOL}	Any terminal to case, t = 1 min	2500	V			
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +175	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V _{BR}	I _R = 200 μA	600	-	-		
Forward voltage	V _{FM}	I _F = 150 A	-	1.36	1.7	V	
Forward voltage		I _F = 150 A, T _J = 150 °C	-	1.18	-		
		V _R = 600 V	-	0.2	100		
Reverse leakage current	I _{RM}	$T_{\rm J} = 125 \ ^{\circ}{\rm C}, \ V_{\rm R} = 600 \ {\rm V}$	-	51	-	μA	
		$T_{J} = 150 \ ^{\circ}C, V_{R} = 600 \ V$	-	156	-		

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Reverse recovery time	+	$T_J = 25 \ ^\circ C$		-	76	-	ns
neverse recovery time	t _{rr}	T _J = 125 °C		-	107	-	
Pook receiver aurrent	I _{RRM}	T _J = 25 °C	I _F = 150 A, di _F /dt = 1000 A/μs, V _R = 400 V	-	24	-	A
Peak recovery current		T _J = 125 °C		-	60	-	
Reverse recovery charge	0	T _J = 25 °C	n	-	0.9	-	
neverse recovery charge	Q _{rr}	T _J = 125 °C	25 °C		4.1	1 - ^{µC}	μC
Junction capacitance	CT	V _R = 600 V, f =	= 1 MHz	-	126.5	-	pF

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Thermal resistance junction to case, per diode			-	-	0.35		
Thermal resistance junction to case, per module	R _{thJC}		-	-	0.175	°C/W	
Thermal resistance case to heatsink, per module	R _{thCS}	Flat, greased surface	-	0.05	-		
Weight			-	30	-	g	
		Torque per diode	-	-	1.1 (9.7)	Nm (lbf.in)	
Mounting torque		Torque to heatsink	-	-	1.8 (15.9)	Nm (lbf.in)	
Case style				SO	Г-227	•	

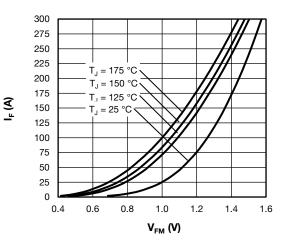


Fig. 1 - Typical Forward Voltage Drop Characteristics

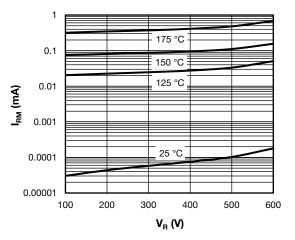


Fig. 2 - Typical Values of Reverse Current



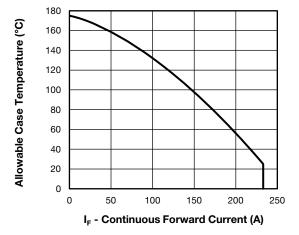


Fig. 3 - Maximum Allowable Case Temperature vs. Average Forward Current (Per Diode)

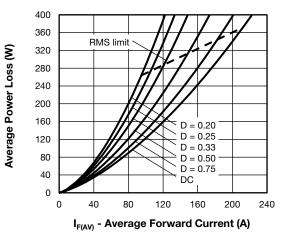


Fig. 4 - Average Power Loss vs. Average Forward Current

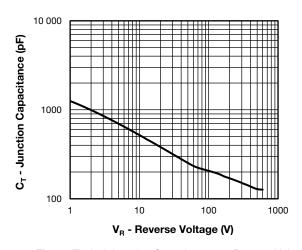


Fig. 5 - Typical Junction Capacitance vs. Reverse Voltage

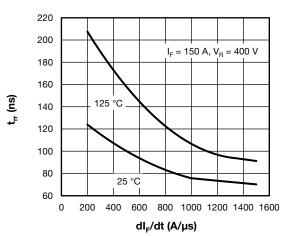


Fig. 6 - Diode Reverse Recovery Time vs. dl_Fdt

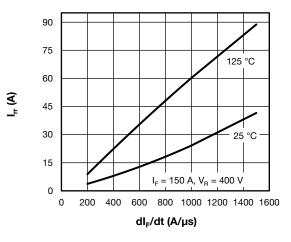


Fig. 7 - Diode Reverse Recovery Current vs. dl_Fdt

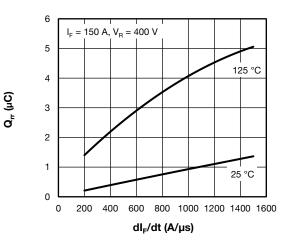


Fig. 8 - Diode Reverse Recovery Charge vs. dl_Fdt

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www.vishay.com 1 Z_{thJC} - Thermal Impedance Junction to Case (°C/W) 0.1 0.50 0.20 0.10 0.01 0.05 0.02

0.001 0.0001 0.0001 0.0001 0.0001 0.001 0.001 0.01 0

Fig. 9 - Maximum Thermal Impedance Junction to Case

ORDERING INFORMATION TABLE Device code VS- U5F H

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vice code	VS-	U5F	н	300	F	Α	60		
	1	2	3	4	5	6	7		
	1 -		,	niconduo					
	2 - 3 -			5 FRED st FRED					
	4 -	· Cur	rent rati	ng per r	nodule	(300 = 3	300 A)		
	5 -	F=	circuit d	configura	ation (tv	vo sepa	rate dio	des, parallel pin-out)
	6 -	- Pac	kage in	dicator (SOT-22	27 stanc	lard ins	ulated base)	

- Voltage rating (60 = 600 V)

CIRCUIT CONFIGURATION						
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING				
Two separate diodes, parallel pin-out	F	Lead Assignment				

LINKS TO RELATED DOCUMENTS					
Dimensions		www.vishay.com/doc?95423			
Packaging information		www.vishay.com/doc?95425			
Devisions 10 Mars 2000		De sum ent Number 20040			
Revision: 19-May-2022	4	Document Number: 9694			

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SOT-227 Generation 2

DIMENSIONS in millimeters (inches)



Note

• Controlling dimension: millimeter



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